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Japanese Kokai Patent Application No. Hei 6[1994]-163481

Translated from Japanese by the Ralph McElroy Translation Company
910 West Avenue, Austin, Texas 78701 USA

Code: 598-69007

JAPANESE PATENT OFFICE

PATENT JOURNAL

KOKAI PARENT APPLICATION NO. HEI 6[1994]-163481

Technical Disclosure Section

Int. Cl. ⁵ :	H 0 1 L 21/302
Sequence Nos. for Office Use:	9277-4M A 9277-4M F 9277-4M
Application No.:	Hei 4 [1992]-333638
Application Date:	November 18, 1992
Publication date:	June 10, 1994
No. of claims	2 (Total of 7 pages)
Examination Request:	Not requested

SEMICONDUCTOR DRY ETCHING METHOD

Inventors:	Atsushi Omuro Nippon Denso K. K. 1-1 Showa-cho, Kariya-shi Aichi-ken
	Yoshikazu Sakano Nippon Denso K. K. 1-1 Showa-cho, Kariya-shi Aichi-ken

Kenji Kondo
Nippon Denso K. K.
1-1 Showa-cho, Kariya-shi
Aichi-ken

Shoji Miura
Nippon Denso K. K.
1-1 Showa-cho, Kariya-shi
Aichi-ken

Kin Takatoshi
103 Coopo Aaikawa
3827-1 Nakatsu,
Aikawa-cho
Aiko-gun, Kanagawa-ken

Tetsuhiko Mikame
306 Sofitel
1212 Gobu, Narita-shi
Chiba-ken

Applicant:

000004260
Nippon Denso K. K.
1-1 Showa-cho, Kariya-shi
Aichi-ken

Agent:

Osamu Fujitani,
patent attorney

[There are no amendments to this patent.]

Abstract

Objective

The objective is to present a method for forming a trench on a silicon substrate through control.

Configuration

A reactive ion etching (RIE) was used as a dry etching device; and HBr as a Br family gas, SF_6 as a halogen family gas, and a N_2 gas were used for the etching gas. As a result, it was possible to set the angle of the side wall to a desired angle ranging from approximately 60° to 90° by means of N_2 flow rate control without lowering SiO_2 selection ratio; besides, it was also possible to reduce the etching residue by SF_6 . Surface of the side walls of the trench were very smooth, and the bottom was kept well-shaped under a fairly wide range of conditions. The etching rate was approximately 800 nm/min, yielding a sufficiently practical production level. A method capable of controlling the angle of the side walls and creating a trench at a high reproducibility rate through the utilization of the etching gas mixture of the present application example while controlling the flow rate to reduce etching residue drastically was presented.

	③ エッチングガス	④ 側壁角度	⑤ 対SiO ₂ 選択比	⑥ ボウイング	⑩ エッチング 速度	⑫ エッチング 残膜量
① 実施例	HBr/SF ₆ /N ₂	87°	25	無 ⑦	800 nm/分	17nm/Chip
② 比較例①	HBr	88°	25	無 ⑦	750 nm/分	40nm/Chip
② 比較例②	HBr/SF ₆	88°	25	無 ⑦	800 nm/分	30nm/Chip
② 比較例③	HBr/SiF ₄ /HeO ₂	x	52	-	1200 nm/分	100 以上 ⑧
② 比較例④	HBr/Cl ₂ /HeO ₂	81°	21	有 ⑧	250 nm/分	20nm/Chip ⑪

- Key: 1 Present application example
 2 comparative example
 3 Etching gas
 4 Side wall angle
 5 SiO₂ selection ratio
 6 Bowing
 7 Etching rate
 8 Etching residue
 9 No
 10 Yes
 11 Min
 12 Unit
 13 Or more

Claims

1. Dry etching method for etching a silicon substrate, characterized in that
 a mixed gas comprising a gas containing bromine,
 a gas containing a halogen element, and
 a nitrogen gas is used; and the etching rate and the angle of the trench are controlled by setting the flow rate of the aforementioned nitrogen gas to a prescribed ratio relative to the flow rate of the aforementioned bromine-containing gas.

2. Dry etching method described under Claim 1 characterized in that, the nitrogen gas content is 1-50% or less relative to that of the bromine-containing gas.

Detailed explanation of the invention

[0001]

Industrial application field

The present invention pertains to a method for shaping a trench and a pit by means of dry etching on a substrate, which is useful in the area where Si is used as a material to produce products, particularly, DRAM semiconductor devices.

[0002]

Prior art

The deep recess (trench) created by selectively etching deep into the surface, the object the present invention intends to achieve, is needed to realize high level of integration and voltage resistance of semiconductors. From the viewpoint of semiconductor production process and semiconductor characteristics, as shown in Figure 1 (a), it is preferable that the sides taper slightly and smoothly, and the bottom forms a semicircle in terms of the shape, necessitating the establishment of the shaping technology for this. Undesirable shapes are those shown in Figures 1 (b) through (h).

[0003]

Conventionally, dry etching on Si is not limited to a trench (the same for a pit, but only trenches will be mentioned hereinafter); wherein, as disclosed in Japanese Kokoku Patent No. Sho 57 [1982]-11954 and Japanese Kokoku Patent No. Sho 59 [1984]-22374, a gas containing fluorine (will be designated as "F family gas" hereinafter), a gas containing chlorine (will be designated as "Cl family gas" hereinafter), and a gas containing bromine (will be designated as "Br family gas" hereinafter) are being used widely. In general, as shown in Figure 2, after an insulating SiO_2 mask (202) is formed on an Si substrate (201) (Figure 2 (a)), a pattern is created on the mask (Figure 2 (b)), and etching is applied (Figure 2 (c)) to form a trench. Here, processes, such as integrated circuit formation, are omitted.

[0004]

At the present time, while attempts are being made to realize the formation of a trench using an RIE (Reactive Ion Etching) device and applying an etching gas atmosphere made of a Br family gas, an F family gas, and a Cl family gas, for example, no method reliable enough to be used for production is yet known. Some known methods report that the shape of the side walls of a trench can be controlled when an SiCl_4 etching gas and an inert gas are mixed, and dry etching is applied while the gas pressure is controlled.

[0005]

Problem to be solved by the invention

Incidentally, when forming the trench in Figure 2 (c), not only the Si substrate (201) part but also a part of the SiO_2 mask (202) are made thinner by the etching during said process. The indication of the unlikeliness of the reduction of said mask is the " SiO_2 selection ratio" wherein, the greater the value is, the more easily the trench is created. When the value of the SiO_2 selection ratio is small, the mask will be gone before a prescribed depth is achieved by etching, and the Si on the substrate ends up being eroded away. Therefore, there is a problem that while an etching gas with greater SiO_2 selection ratio is in demand, F family gases usually have a low SiO_2 selection ratio, and isotropic etching, by which the reaction proceeds in all directions, is likely to occur.

[0006]

In addition, as semiconductor devices gain diversity and higher performance, the etching residue needs to be reduced during the formation of the trench in order to improve the yield. As shown in Figure 4, mechanism of the formation of etching residue can be explained as the adherence of dust and particles (404) onto the parts (403) where the Si is exposed on the mask under the condition of (a) prior to etching, or pieces of the mask and the products of the reaction (substances difficult to etch) formed at the time of etching are adhered during the etching, so that normal etching is hindered and ultimately the

conditions (405) shown in Figure 4 (b) are created. This is referred to as black Si or Si black, which creates a problem of deterioration in yield. In general, there is a problem that the amount of black Si increases in the order of F family gases, Cl family gases, and Br family gases. However, there is an advantage that the further forward in the aforementioned order, the better the shape of the side walls becomes.

[0007]

On the other hand, as disclosed in Japanese Kokoku Patent No. Sho 59 [1984]-67635, a general method in which the Si is etched vertically is presented in the prior art. However, depth of the trench was 5 μm or so at most with this method, and when an attempt was made to etch any deeper than that, the shape of the trench lost uniformity. On the contrary, when the shape was to be perfected, the problem of residue occurred. Thus, [said method] had not necessarily reached the level at which trenches having a uniform shape at a highly accurate satisfactory level could be formed. Accordingly, there are cases in which various kinds of etching gases are mixed in order to make best use of their characteristics. However, no etching method which would solve all of the problems and lead to production has yet been suggested.

[0008]

In addition, although U.S. Patent No. 4784720 discloses that products are adhered selectively onto the side walls of a trench in order to control the shape of the trench, a method in which

the shape is controlled through selective adhesion of the aforementioned etching residues is likely to generate etching residues. Leaving the residues alone would lead to the problem of deteriorated yield due to leakage and insufficient voltage breakdown resistance. Thus, processes need to be added to remove [the residues]. In addition, in the aforementioned report providing that SiCl_4 and an inert gas are mixed and the gas pressure can be used to control the shape of the side walls of the trench, there is no specification of the inert gas, nor is there any mention of other etching gases.

[0009]

The purpose of the present invention is to achieve efficient and highly accurate formation of a reproducible well-shaped trench while solving the aforementioned problem at the same time.

[0010]

Means to solve the problem

In order to solve the aforementioned problem, a silicon substrate etching gas is prepared by mixing a gas containing bromine (designated as "Br family gas" hereinafter), a gas containing halogen elements (designated as "X family gas" hereinafter), and a gas containing nitrogen (designated as " N_2 family gas" hereinafter), and dry etching is carried out. In such case, the flow rate of the N_2 gas is adjusted according to the intended trench shape.

[0011]

Function

When etching is performed with various kinds of parameters, which will be clarified later in an application example, set to appropriate values using the etching gas having the aforementioned composition, etching on the Si substrate is advanced primarily by the Br family gas; the X family gas plays the role of removing the etching residues by means of volatilization; and the N₂ gas controls the Br family gas and the X family gas to prevent over-reaching, which in turn plays the role of controlling the shape in order to achieved the intended trench.

[0012]

Effect of the invention

As it will be clarified in the application example later, the angle of the side walls of the trench was controlled by controlling the flow rate of the N₂ gas without deteriorating the SiO₂ selection ratio. In addition, apart from what was just said, residues were reduced drastically by the X family gas. As a result, the intended trench formation method was able to be presented.

[0013]

Application example

no manifest

The present invention will be explained based below on a specific application example. The RIE (Reactive Ion Etching) device shown in schematic cross section in Figure 3 was used as the dry etching device. In Figure 3, an etching chamber (301) is provided with an upper electrode (304) and a lower electrode (305), a target Si substrate (308) is placed on said lower electrode (305), an etching gas to be described below is introduced through a gas inlet (302) and discharged from an exhaust opening (303). A 13.56 MHz power is supplied between said electrodes from a high-frequency power source (306) in order to generate gas plasmas for etching the Si substrate. Furthermore, said RIE device is of the magnetron type, wherein a magnetic coil (307) is provided around the etching chamber.

[0014]

The etching gases used with the aforementioned RIE device in the present application example are HBr as the Br family gas, SF₆ as the X family gas, and N₂ gas.

[0015]

Etching was applied to the Si substrate using the aforementioned gas composition with the SF₆ flow rate set to 2 and 3 (SCC), the high-frequency power of the RIE device to 500 (W), pressure of the mixed gas to 100 (mtorr), and magnetic

intensity of the coil indicated by 307 in Figure 3 to 55 (Gauss) while changing the flow rate of the N_2 gas; and the angles (102) of the side walls of the trench were then measured. As a result, a proportional relationship was found to be present in the area where the wall is perpendicular as shown in Figure 5, indicating that the side wall angle can be set to a desired angle between approximately 60 degrees and 90 degrees by adjusting the flow rate of the N_2 gas. Furthermore, as shown in Figure 6, the SiO_2 selection ratio also changes according to the flow rate of the N_2 gas, and it increases as the flow rate increases to the advantage of the formation of the trench.

[0016]

[The mechanism of] said function of the N_2 gas can be inferred as follows. N_2 is broken up by the plasma into N radicals during the etching, and these [radicals] react with Si or etching product in the chemical vapor to create SiN. This [SiN] covers the side walls, which prevents etching from advancing excessively and helps control the angle of the side walls at the same time. Because it also covers the SiO_2 mask at the same time, SiO_2 is prevented from being etched, and the SiO_2 selection ratio is increased as a result.

[0017]

In addition, it has been also confirmed that the surfaces of the side walls become extremely smooth when the N_2 gas is mixed, indicating that it is an effective way to improve the reliability.

[0018]

As shown in Figure 7, it was evident that the etching residues decreased as the SF_6 flow rate increased and disappeared with a relatively small SF_6 flow rate. The amount of etching residue was obtained by comparing the number of residual [particles] per 1-cm-square chip with 10 μm pattern width. As shown in Figure 8, said mechanism can be explained as follows: even if a small object (803) which did not get etched was present on an Si substrate (801), SF_6 is broken up into active F radicals (804) in the plasma, and [these] react with the small object (803) and volatilize (805) it. However, it was found that with the flow rate which eliminates the residues completely, the SiO_2 selection ratio becomes relatively small, that is, approximately 10. This is a disadvantage when creating a deeper trench, but adjustments can be made to optimize it depending on the extension of the trench to be created.

[0019]

With respect to the shape of the trench, it is preferable that the bottom takes an arc (bottom round) shape for the sake of the relaxation of the field and the stress at the bottom part. A variety of tests were conducted regarding said shape. As a result, it was confirmed that desirable bottom shape was maintained under a fairly wide range of conditions, as shown in Figure 9. It was confirmed that N_2 gas demonstrated its effect also when the low rate was within the range of 0-30 (SCCM). In addition, the etching rate, that is, approximately 800 nm/min.

(Figure 12), was confirmed to meet the level for practical production sufficiently.

[0020]

When the etching gas was replaced by another gas in order to compare the amounts of etching residues, the results shown in Figure 10 were obtained. It was clear that the configuration of the present application example as described above was most suitable for trench formation. Figure 11 shows the etching conditions in the application example and the comparative examples.

[0021]

Based on a general view over the aforementioned findings, as shown in Figure 2, it was possible to present a method capable of controlling the side wall angle while reducing etching residues drastically by controlling the flow rate of the etching gas having the configuration of the present application example in order to create a trench at a high reproducibility rate.

[0022]

Furthermore, the X family gas need not be SF_6 , and other gases, such as CF_4 , C_2F_6 , CHF_3 , NF_3 , among others, may be used. In addition, the same effect can be achieved by means of an ECR (Electron Cyclotron Resonance) device instead of the RIE device.

Brief description of the figures

Figure 1 shows cross sections showing various trench shapes, of which (a) is a cross section showing an ideal shape, and (b) through (h) are cross sections showing undesirable shapes.

Figure 2 is a diagram showing simplified trench formation process.

Figure 3 is a cross section showing the schematic configuration of the magnetron RIE (Reactive Ion Etching) device used in the application example of the present invention.

Figure 4 are diagrams showing the mechanism of the generation of etching residues schematically.

Figure 5 is a diagram showing the N_2 flow rate dependency characteristic of the trench side wall angle of the sample used in the application example.

Figure 6 is a diagram showing the N_2 flow rate dependency characteristic of the SiO_2 selection ratio of the sample used in the application example.

Figure 7 is a diagram showing the SF_6 flow rate dependency characteristic of the etching residues.

Figure 8 is a diagram showing the mechanism of the reduction of etching residues by SF_6 schematically.

Figure 9 is a diagram showing the range of setting for the formation of well-shaped trench used in the application example.

Figure 10 is a diagram showing the result of the comparison of the amounts of etching residues between the application example and other etching gases.

Figure 11 is a diagram showing the etching conditions of the application example and the comparative examples.

Figure 12 is a diagram showing the results of the comparison with the etching gases other than those of the application example.

Explanation of reference numerals

- 101. Si substrate
- 102. Trench side wall angle
- 201. Si substrate
- 202. SiO₂ mask
- 203. SiO₂ mask thinned by etching
- 301. Etching chamber of the RIE device
- 308. Si substrate to be etched
- 401. Si substrate
- 402. SiO₂ mask
- 403. Window on the mask pattern (part to be etched)
- 404. Residue (deposit)
- 405. Etching residue (black Si)
- 801. Si substrate
- 802. SiO₂ mask
- 803. Small object, such as dust, which does not get etched
- 804. Fluoride radical
- 805. Volatile substance

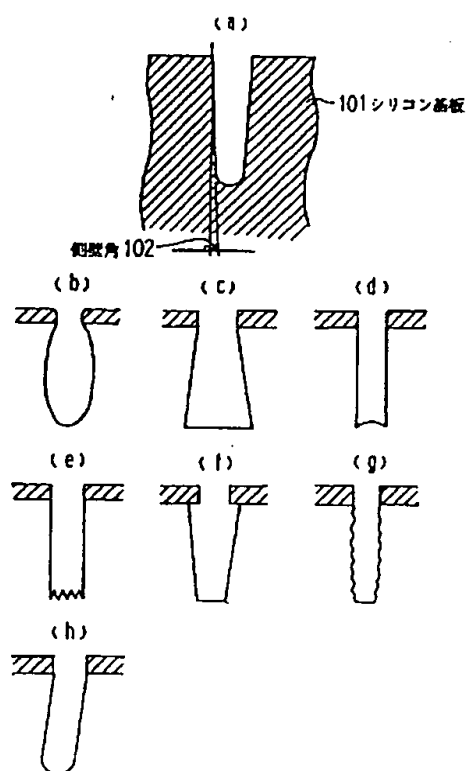


Figure 1

Key: 101 Silicon substrate
102 Side wall angle

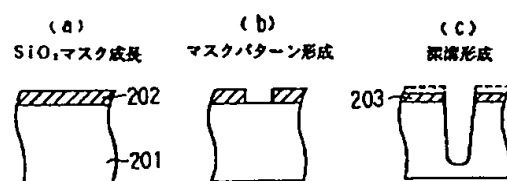


Figure 2

Key: a SiO_2 mask growth
 b Mask pattern formation
 c Trench formation

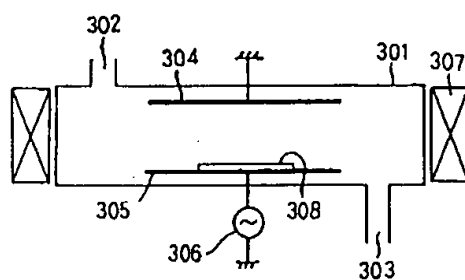


Figure 3

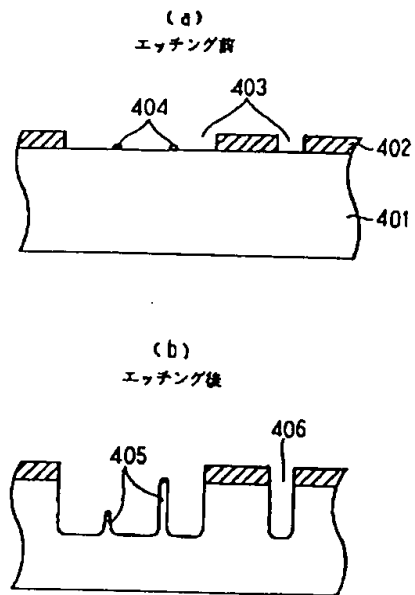


Figure 4

Key: a Before etching
b After etching

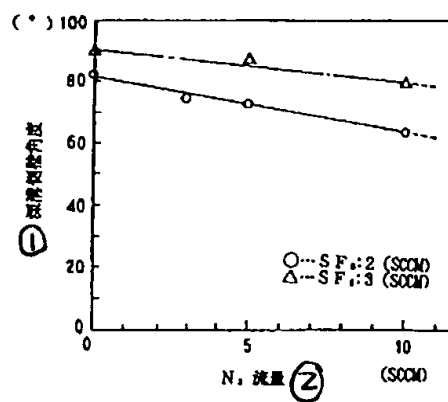


Figure 5

Key: 1 Trench side wall angle
 2 N₂ flow rate

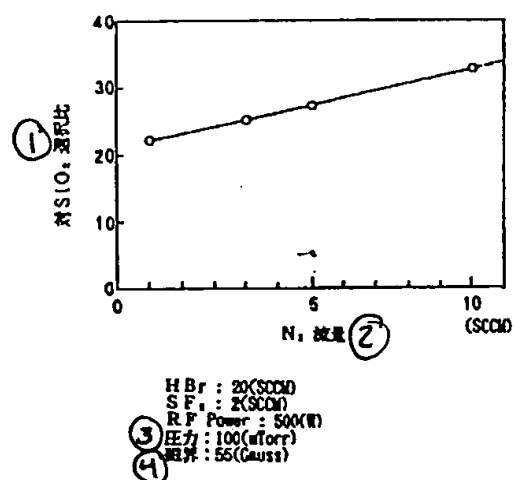


Figure 6

Key: 1 SiO_2 selection ratio
 2 N_2 flow rate
 3 Pressure
 4 Magnetic field

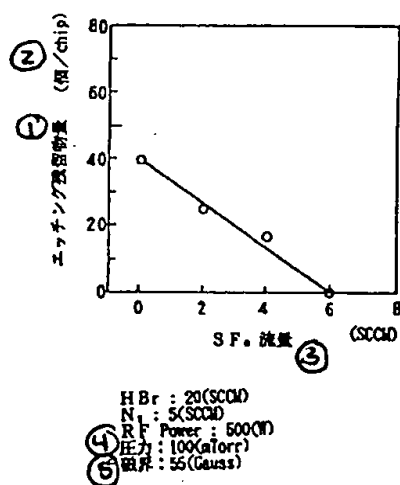


Figure 7

Key: 1 Amount of etching residues
 2 Unit(s)
 3 SF₆ flow rate
 4 Pressure
 5 Magnetic field

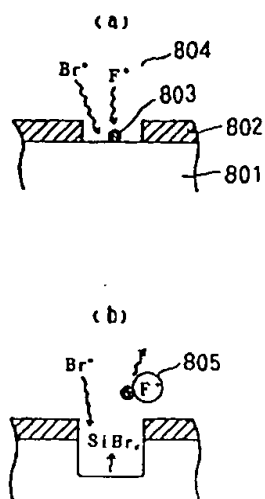


Figure 8

要①因	設定値②
HBr 流量 (SCCM)	10 ~ 100
SF ₆ 流量 (SCCM)	2 ~ 10
N ₂ ② 流量 (SCCM)	3 ~ 10
高周波電力 (W) ③	200 ~ 600
ガス圧 ④ (mTorr)	50 ~ 150
磁界強度 ⑤ (Gauss)	0 ~ 100

Figure 9

Key: 1 Factor
 2 Flow rate
 3 High-frequency power
 4 Gas pressure

- 5 Intensity of magnetic field
6 Value to be set

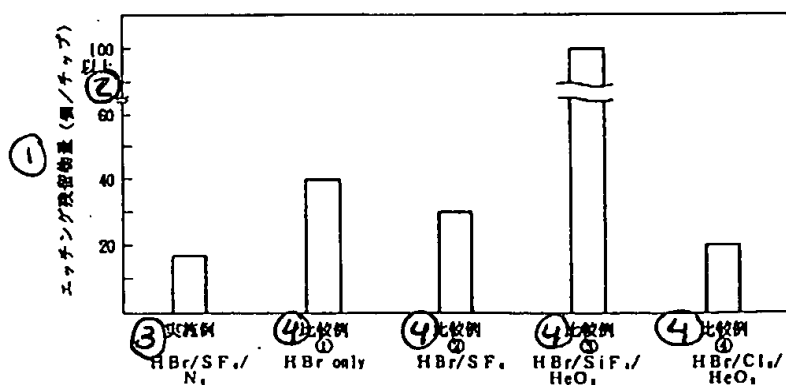



Figure 10

- Key: 1 Amount of etching residues
2 Or more
3 Application example
4 Comparative Example



① 実施例及び 比較例	⑤ 実施例 HBr/SF ₆ / N ₂	⑥ 比較例① 比較例② 比較例③ 比較例④			
		HBr only	HBr/SF ₆	HBr/SiF ₄ / HeO ₂	HBr/Cl ₂ / HeO ₂
② {	HBr 流量 (SCCM)	80	20	22	30
	SiF ₄ 流量 (SCCM)	—	—	5	—
	HeO ₂ 流量 (SCCM)	—	—	10	4
	N ₂ 流量 (SCCM)	—	—	—	—
	SF ₆ 流量 (SCCM)	—	2	—	—
	Cl ₂ 流量 (SCCM)	—	—	—	10
	RF Power (W)	400	400	420	150
③	圧力 (mTorr)	100	100	100	20
④	磁界強度 (Gauss)	55	55	55	75

Figure 11

- Key: 1 Application example and comparative example
 2 Flow rate
 3 Pressure
 4 Intensity of magnetic field
 5 Application example
 6 Comparative Example

	③ エッチングガス	④ 側壁角度	⑤ 対SiO ₂ 選択比	⑥ Bowling ボーイング	⑦ エッチング 速度	⑧ エッチング 残留物
① 当実施例	HBr/SF ₆ /N ₂	87°	25	⑨ 無 no	800 nm/分	17個/Chip ⑫
② 比較例①	HBr	88°	25	⑨ 無 no	750 nm/分	40個/Chip ⑫
比較例②	HBr/SF ₆	88°	25	⑨ 無 no	800 nm/分	30個/Chip ⑫
比較例③	HBr/SiF ₄ /HeO ₂	×	52	—	1200 nm/分	100 以上 ⑬
比較例④	HBr/Cl ₂ /HeO ₂	91°	21	⑩ 有 yes	350 nm/分	20個/Chip ⑬

Figure 12

- Key: 1 Present application example
 2 comparative example
 3 Etching gas
 4 Side wall angle
 5 SiO₂ selection ratio
 6 Bowling
 7 Etching rate
 8 Etching residue
 9 No
 10 Yes
 11 Min
 12 Unit
 13 Or more